GENERAL DESCRIPTION

The LDR100SB utilizes the most advanced design and process technologies. These features provide the most consistent and reliable chip and package combination designed, built and tested specifically for L-Band radar. The device is common base input/output matched in a hermetic package. Gold metallization and diffused emitter ballasting provide high reliability.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C Case Temperature 350

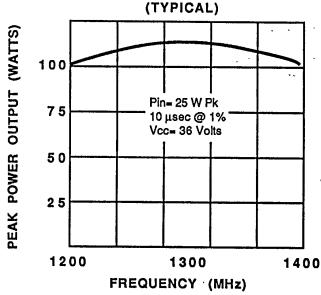
Maximum Voltage and Current
BVces Collector to Emitter Voltage
BVebo Emitter to Base Voltage
Collector Current

Collector to Emitter Voltage 50 V
Emitter to Base Voltage 3.5 V
Collector Current 10 A

Maximum Temperatures Storage Temperature Operating JunctionTemperature

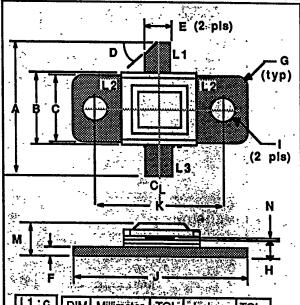
-65 to +200 °C +200 °C

POWER OUTPUT VS FREQUENCY (TYPICAL)



LDR100SB 100 WATTS - 36 VOLTS 1200/1400 MHz

RADAR



24 28 2 31 2 4 C. 1										
.1 : c	DIM	Millimeter:	TOL	inches	TOL					
2 : b	Α	20.32	.76		.030					
.3 : e	* B	10.16	.13	.400	.005					
	C	9.78	.13	.385	.005					
	D	45 O 25	50	45 0	~ 5 0					
•	LE	3.81 ₹	.13	.150	.005					
	F.	1.52	.13	.060	.005					
	G	1.52 R	.13	-060 R	.005					
	<u>H</u>	3.05	.13		.005					
		~3.30DIA	.13	7130 DIA	.005					
	J	22.86	.13	.900	.005					
-	L K	16.51	.13	.650	.005					
	L M	5.46	REF	.215	REF					
		0.13	.02	.005	.001					

TYPICAL AMPLIFIER LINE UP
Vcc= 36 Volts
Frequency Range= 1200-1400 MHz

LDR30LA

W
LDR30LA

LDR100SB

490 Race Street, San Jose, CA 95126 Phone (408) 294-4200, TWX (910) 338-2172 Ewenny Rd., Bridgend, Mid Glamorgan, CF31 3LQ, United Kingdom, Phone (0656) 68021

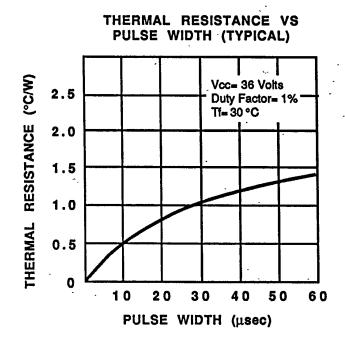
Printed in USA

LDR100SB-2

ELECTRICAL CHARACTERISTICS1

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Pout	Power Output		100			∵Watts
Pin	Power Input	f= 1200-1400 MHz			20 🗀	Watts
Pg .	Power Gain	Vcc= 36 Volts	7.0			ďΒ
η _C	Collector Efficiency	Pulse Width= 10 μsec Duty Factor= 1%		40	argin's real	%
VSWR	Load Mismatch Tolerance				3:1	
BVebo	Breakdown Voltage (Emitter to Base)	le= 15mA	3.5		, 4	Volts
BVces	Breakdown Voltage (Collector to Emitter)	lo= 100mA	50			Volts
h _{FE}	DC-Current Gain	Vce= 5V, lc= 400 mA	10	· · · · · · ·	30.00	
θjc	Thermal Resistance	10 μsec @ 1%			0.5	°C/W

Note 1: Tc = +25°C unless otherwise specified



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